

Product Summary

BV_{DSS}	$R_{DS(on)}$ Max	I_D Max $T_A = +25^\circ C$
60V	5.0Ω @ $V_{GS} = 10V$	200mA
	5.3Ω @ $V_{GS} = 4.5V$	190mA

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant**
- **Halogen and Antimony Free.**

Description and Applications

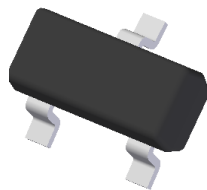
This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

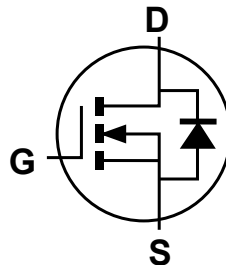
Mechanical Data

- Case: SOT23 (Standard)
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

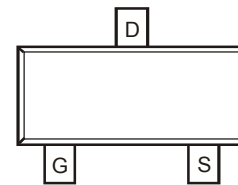
SOT23 (Standard)



Top View



Equivalent Circuit



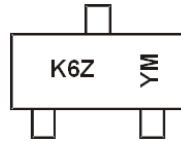
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
MMBF170-7-F	SOT23 (Standard)	3,000/Tape & Reel
MMBF170-13-F	SOT23 (Standard)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



K6Z = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: I = 2021)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	1998	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	J	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0\text{M}\Omega$	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20 ± 40	V
Continuous Drain Current (Note 5)	I_D	200	mA
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	800	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	300	mW
Derating above $T_A = +25^\circ\text{C}$		1.80	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	70	—	V	$V_{GS} = 0\text{V}, I_D = 100\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}	—	—	± 10	nA	$V_{GS} = \pm 15\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.8	2.1	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	2.2 3.2	5.0 5.3	Ω	$V_{GS} = 10\text{V}, I_D = 200\text{mA}$ $V_{GS} = 4.5\text{V}, I_D = 50\text{mA}$
Forward Transconductance	g_{FS}	80	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	22	40	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	11	30	pF	
Reverse Transfer Capacitance	C_{rss}	—	2	5	pF	
Turn-On Delay Time	$t_{D(on)}$	—	—	10	ns	$V_{DD} = 25\text{V}, I_D = 0.5\text{A},$
Turn-Off Delay Time	$t_{D(off)}$	—	—	10	ns	$V_{GS} = 10\text{V}, R_{GEN} = 50\Omega$

- Notes:
- Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout, which can be found on our website at www.diodes.com/package-outlines.html.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

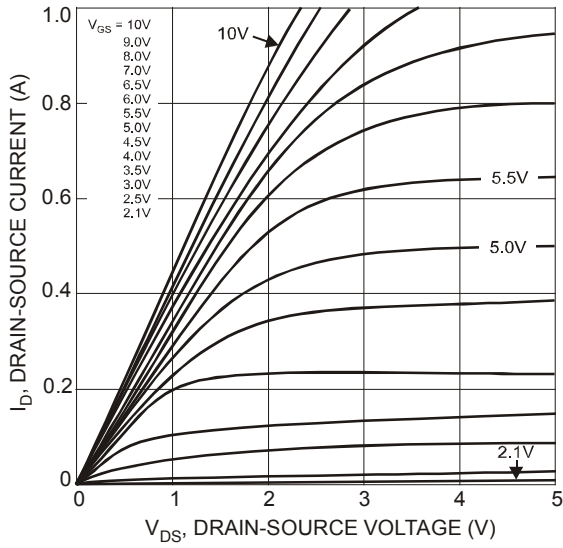


Fig. 1 On-Region Characteristics

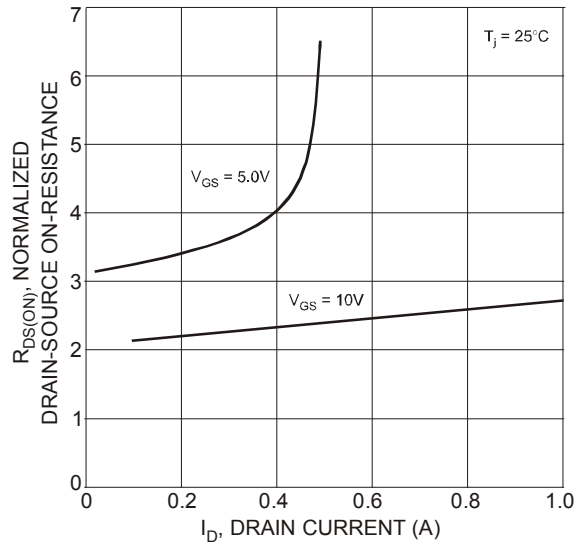


Fig. 2 On-Resistance vs. Drain Current

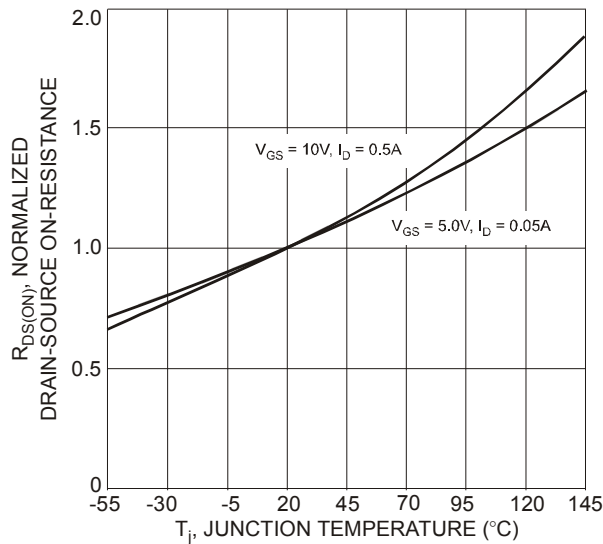


Fig. 3 On-Resistance vs. Junction Temperature

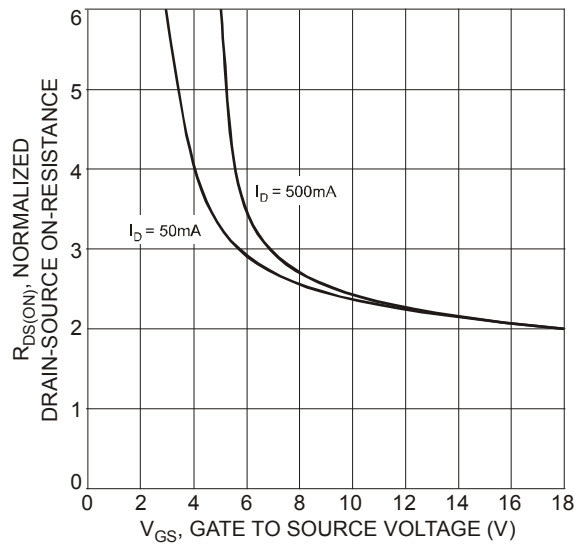


Fig. 4 On-Resistance vs. Gate-Source Voltage

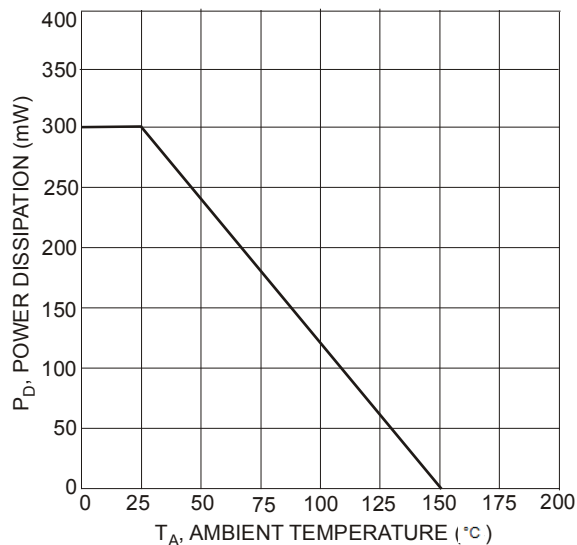
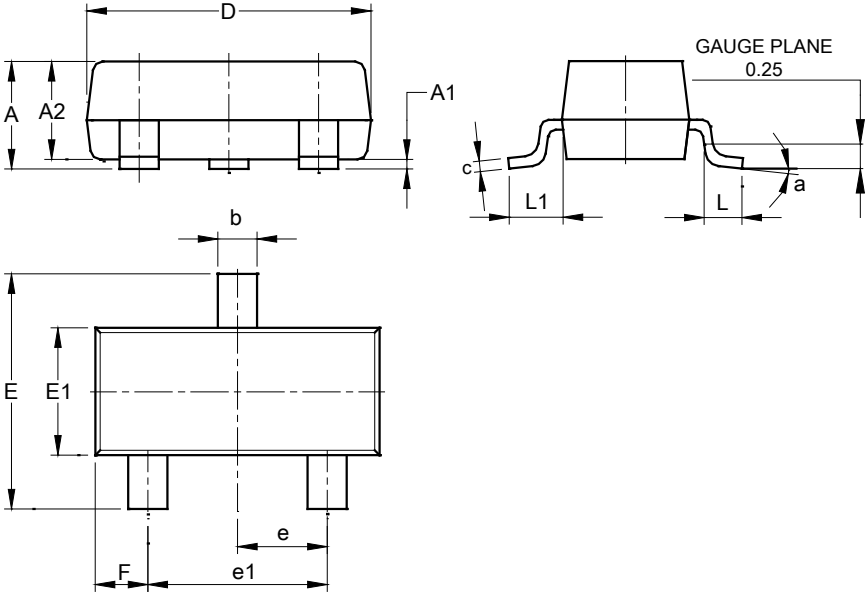


Fig. 5 Max Power Dissipation vs. Ambient Temperature

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

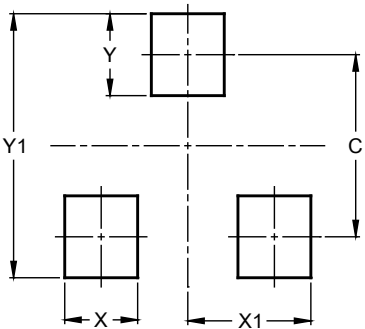


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9